EE C247B – ME C218 Introduction to MEMS Design Spring 2014

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Lecture Module 3: Oxidation & Film Deposition

Lecture Outline

- Reading: Senturia, Chpt. 3; Jaeger, Chpt. 2, 3, 6
  - Example MEMS fabrication processes
  - Oxidation
  - Film Deposition
    - Evaporation
    - Sputter deposition
    - Chemical vapor deposition (CVD)
    - Plasma enhanced chemical vapor deposition (PECVD)
    - Epitaxy
    - Atomic layer deposition (ALD)
    - Electroplating

MEMS Fabrication

Making Mechanical Devices

- How best does one make a mechanical product?
- Assembly line production?
  - Pick and place parts
  - Used for many macroscopic mechanical products
  - Robotic automation greatly reduces cost
- *Problem*: difficult to do this with MEMS-scale parts (but not impossible, as we'll soon see …)
- *Solution*: borrow from integrated circuit (IC) transistor technology
  - Use monolithic wafer-level fabrication methods
  - Harness IC's batch methods, where multiple devices are achieved all at once

Automobile Assembly Line

CMOS Integrated Circuit Wafer

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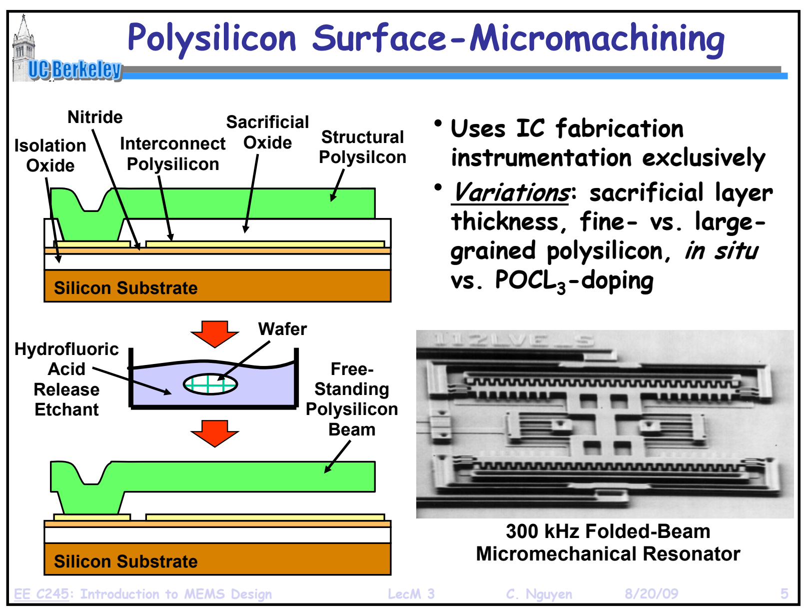

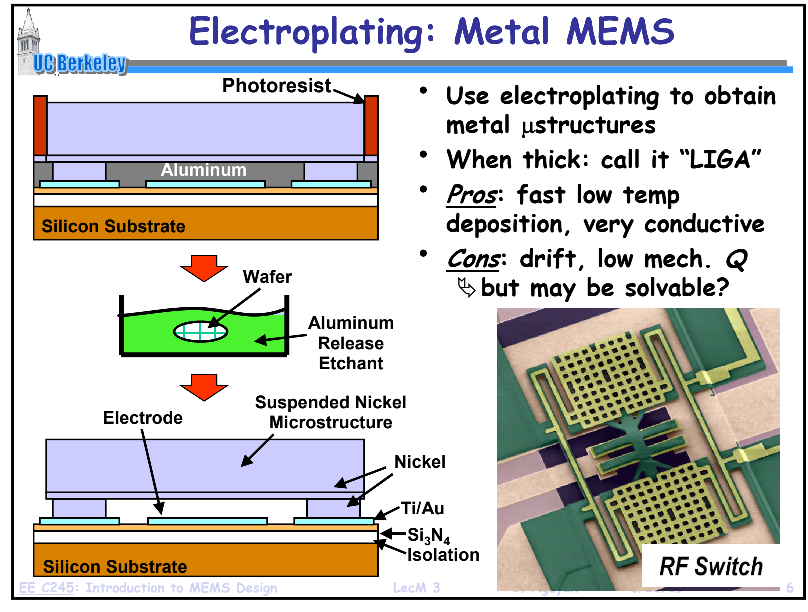

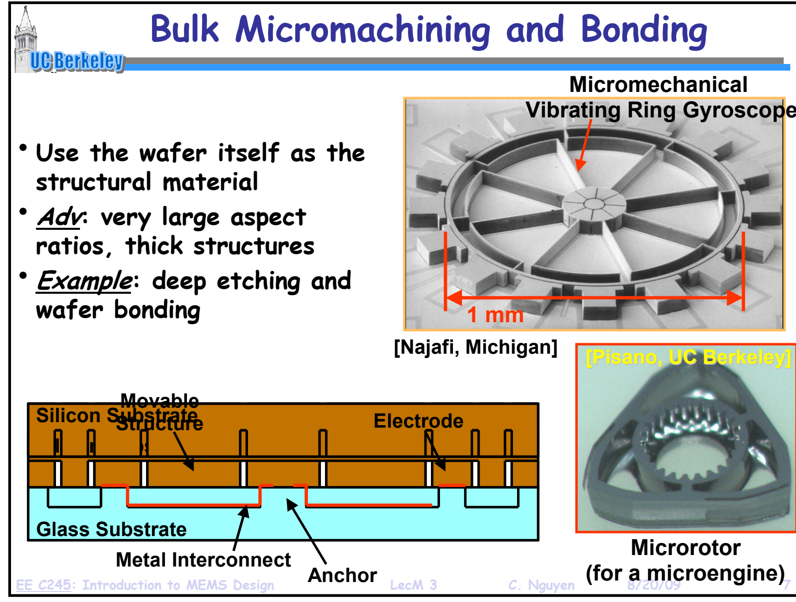

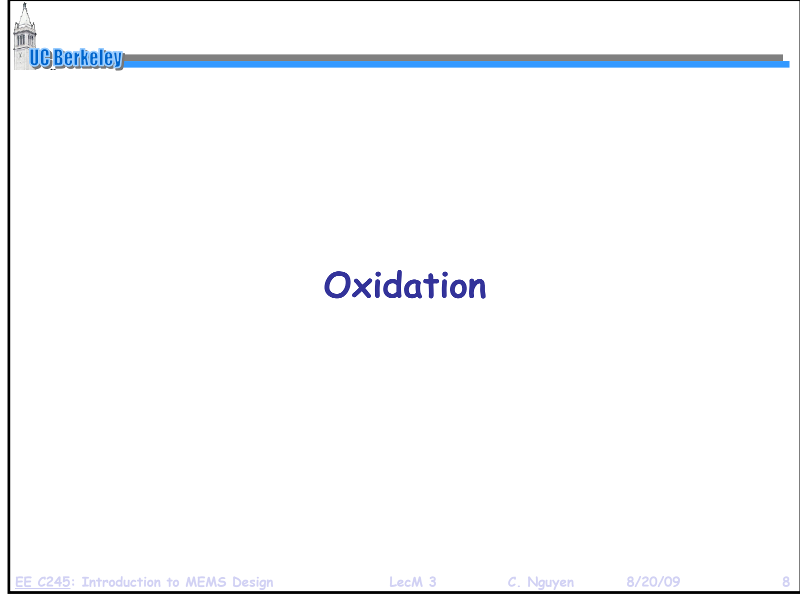

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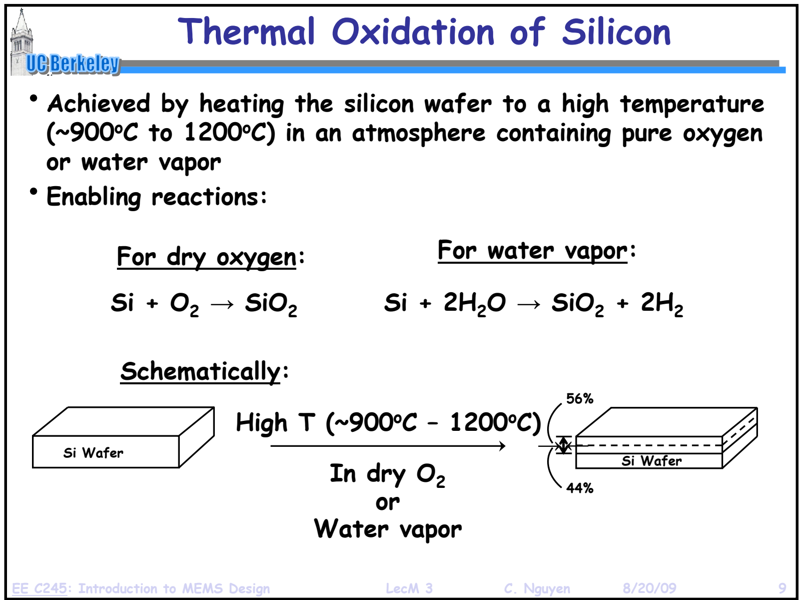

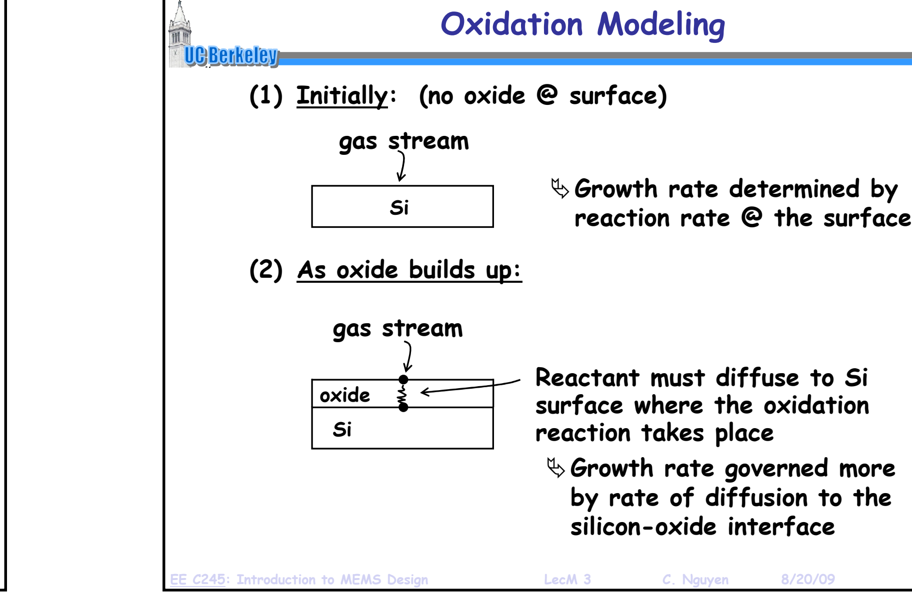

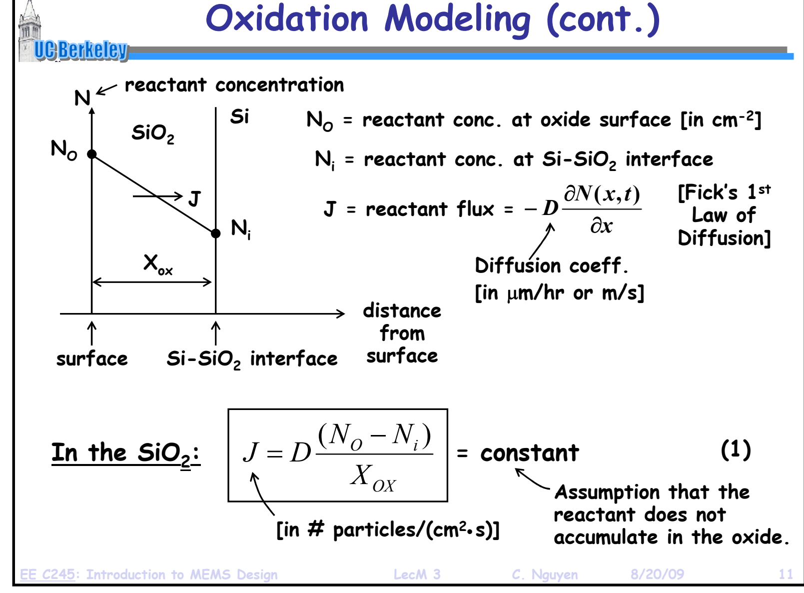

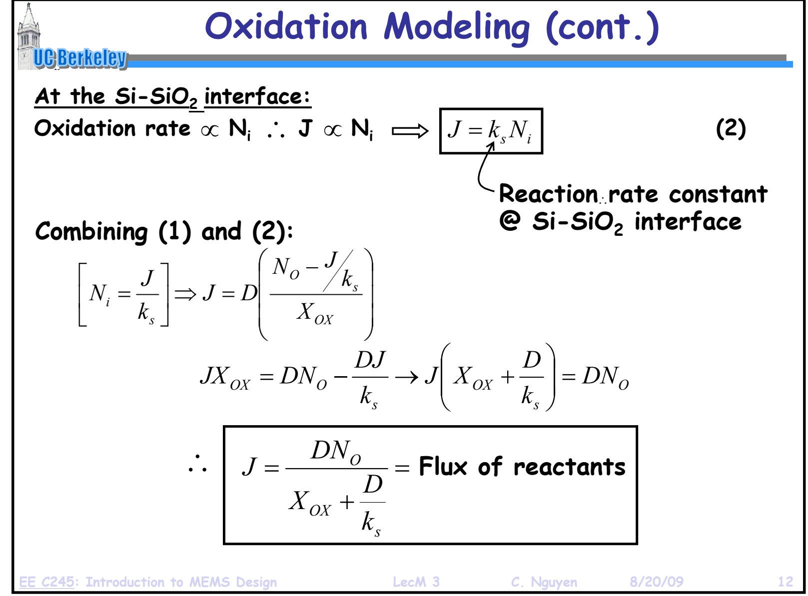

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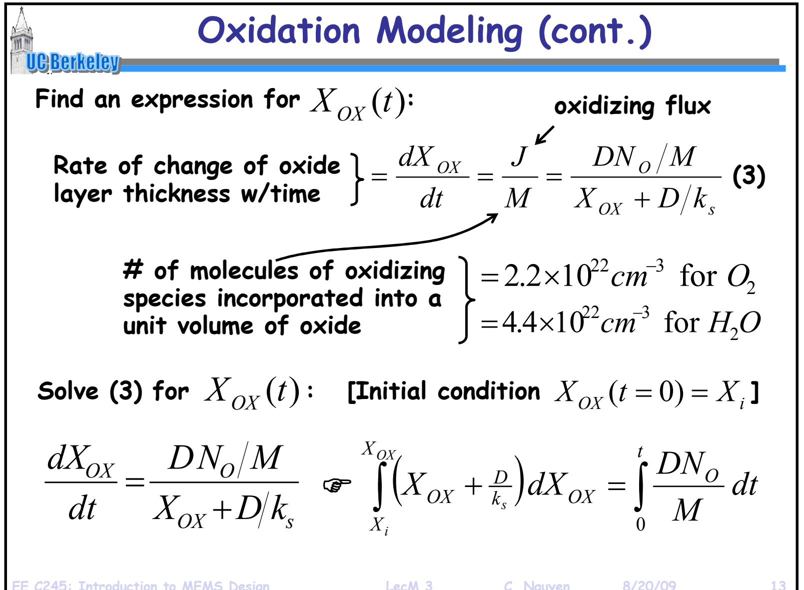

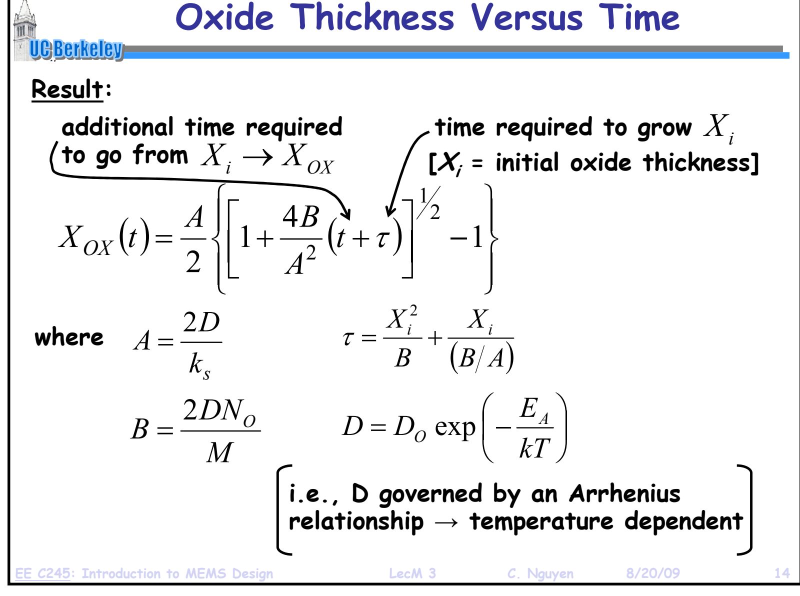

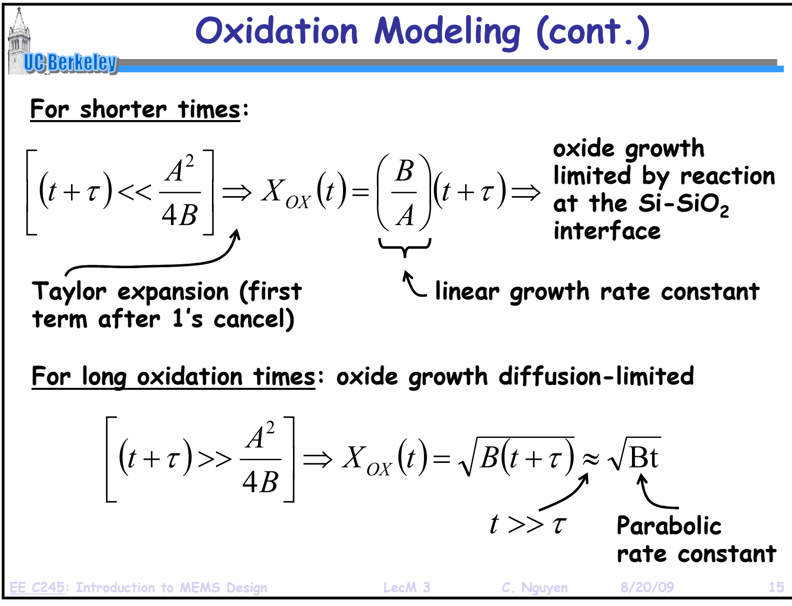

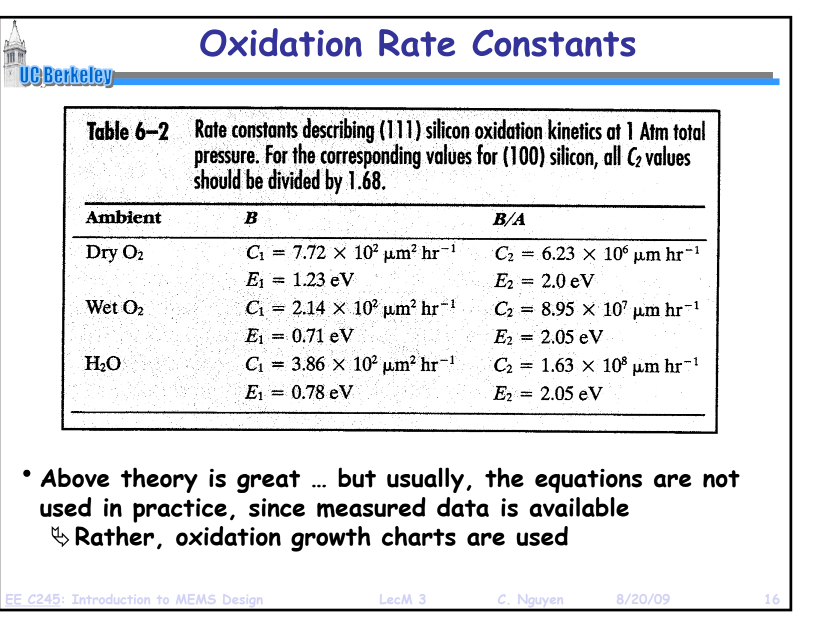

Table 6–2 Rate constants describing (111) silicon oxidation kinetics at 1 Atm total pressure. For the corresponding values for (100) silicon, all C_2 values should be divided by 1.68.

Ambient	B	B/A
Dry O_2	$C_1 = 7.72 \times 10^2\ \mu m^2\ hr^{-1}$	$C_2 = 6.23 \times 10^6\ \mu m\ hr^{-1}$
	$E_1 = 1.23$ eV	$E_2 = 2.0$ eV
Wet O_2	$C_1 = 2.14 \times 10^2\ \mu m^2\ hr^{-1}$	$C_2 = 8.95 \times 10^7\ \mu m\ hr^{-1}$
	$E_1 = 0.71$ eV	$E_2 = 2.05$ eV
H_2O	$C_1 = 3.86 \times 10^2\ \mu m^2\ hr^{-1}$	$C_2 = 1.63 \times 10^8\ \mu m\ hr^{-1}$
	$E_1 = 0.78$ eV	$E_2 = 2.05$ eV

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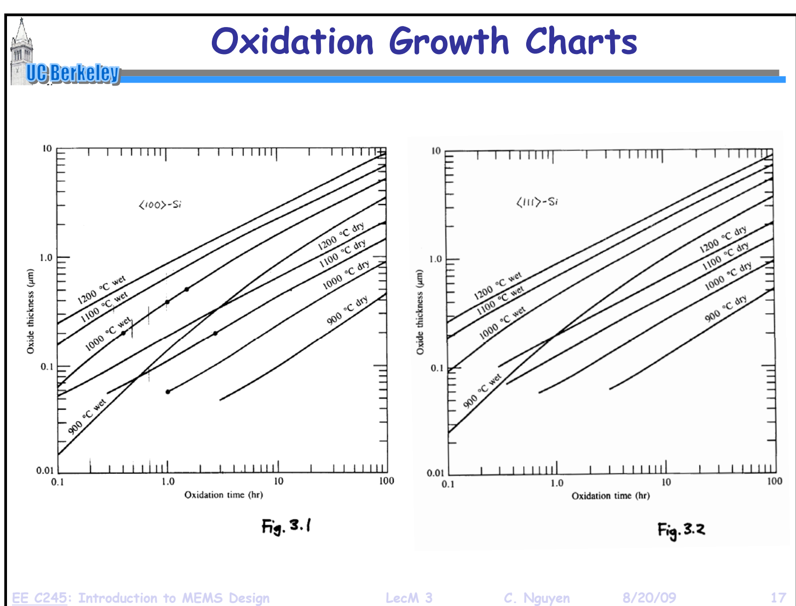
Oxidation Growth Charts
UC Berkeley
<100>-Si
1200 °C wet
1100 °C wet
1000 °C wet
900 °C wet
1200 °C dry
1100 °C dry
1000 °C dry
900 °C dry
Oxide thickness (μm)
Oxidation time (hr)
10
1.0
0.1
0.01
0.1
1.0
10
100
Fig. 3.1
<111>-Si
1200 °C wet
1100 °C wet
1000 °C wet
900 °C wet
1200 °C dry
1100 °C dry
1000 °C dry
900 °C dry
Oxide thickness (μm)
Oxidation time (hr)
Fig. 3.2
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